NSR0340HT1G

Schottky Barrier Diode

Schottky barrier diodes are optimized for very low forward voltage drop and low leakage current and are used in a wide range of dc–dc converter, clamping and protection applications in portable devices. NSR0340H in a SOD–323 miniature package enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Very Low Forward Voltage Drop -415 mV @ 100 mA
- Low Reverse Current $0.4 \mu A @ 25 V V_R$
- 250 mA of Continuous Forward Current
- Power Dissipation of 160 mW with Minimum Trace
- Very High Switching Speed
- Low Capacitance $-C_T = 6 \text{ pF}$
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

Markets

- Mobile Handsets
- MP3 Players
- Digital Camera and Camcorders
- Notebook PCs and PDAs
- GPS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	40	Vdc
Forward Continuous Current (DC)	١ _F	250	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	1.0	A
ESD Rating: Human Body Model Machine Model	ESD	Class 2 Class A	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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40 VOLT SCHOTTKY BARRIER DIODE





AD = Specific Device Code M = Date Code

= Pb–Free Package

CASE 477 STYLE 1

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NSR0340HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
NSVR0340HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Semiconductor Components Industries, LLC, 2014 July, 2014 – Rev. 3

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance Junction–to–Ambient (Note 1) Total Power Dissipation @ $T_A = 25^{\circ}C$	${\sf R}_{ heta {\sf JA}} \ {\sf P}_{\sf D}$	740 160	°C/W mW
Thermal Resistance Junction–to–Ambient (Note 2) Total Power Dissipation @ $T_A = 25^{\circ}C$	R _{θJA} P _D	460 270	°C/W mW
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Mounted onto a 4 in square FR-4 board 10 mm sq. 1 oz. Cu 0.06" thick single-sided. Operating to steady state.
 Mounted onto a 4 in square FR-4 board 1 in sq. 1 oz. Cu 0.06" thick single-sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage $(V_R = 10 V)$ $(V_R = 25 V)$ $(V_R = 40 V)$	I _R		0.2 0.4 1.3	1.0 3.0 6.0	μΑ
Forward Voltage $(I_F = 10 \text{ mA})$ $(I_F = 100 \text{ mA})$ $(I_F = 200 \text{ mA})$	V _F		320 415 470	350 490 590	mV
Total Capacitance ($V_R = 10 V, f = 1 MHz$)	СТ		6.0		pF
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}, I_R = 1.0 \text{ mA}$)	t _{rr}		5.0		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Figure 1. Recovery Time Equivalent Test Circuit

NSR0340HT1G

TYPICAL CHARACTERISTICS













SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 13 MAR 2007

- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.90	1.00	0.031	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A3	0.15 REF		0	.006 RE	REF		
b	0.25	0.32	0.4	0.010	0.012	0.016	
С	0.089	0.12	0.177	0.003	0.005	0.007	
D	1.60	1.70	1.80	0.062	0.066	0.070	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
L	0.08			0.003			
HE	2.30	2.50	2.70	0.090	0.098	0.105	

GENERIC **MARKING DIAGRAM***



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE STYLE 2: NO POLARITY

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SOD-323 CASE 477-02

ISSUE H

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